

1. (Amended) A method for manufacturing a semiconductor device comprising the steps of:  
forming a non-single crystalline semiconductor film on [a substrate having] an insulating surface;  
patterning said semiconductor film into a patterned semiconductor film having peripheral portions;  
disposing a crystallization promoting material in contact with said semiconductor film either before or after said patterning, said crystallization promoting material containing a metal;  
crystallizing said patterned semiconductor film provided with said crystallization promoting material by heating;  
and  
etching the peripheral portions of said patterned semiconductor film after said crystallizing.

6. (Amended) A method for manufacturing a semiconductor device comprising the steps of:  
forming a non-single crystalline semiconductor film on [a substrate having] an insulating surface;  
patterning said semiconductor film into a patterned semiconductor film having a peripheral portion;  
providing defects and/or stress in [a selected region]

said peripheral portion of said patterned semiconductor film  
simultaneously with said patterning step;

disposing a crystallization promoting material in  
contact with said semiconductor film, said crystallization  
promoting material containing a metal;

crystallizing said patterned semiconductor film  
provided with said crystallization promoting material by heating  
wherein said metal segregates in said [selected region]  
peripheral portion during the crystallization; and

etching said [selected region] peripheral portion after  
said crystallizing.

12. (Amended) A method for manufacturing a  
semiconductor device comprising the steps of:

forming a non-single crystalline semiconductor film on  
[a substrate having] an insulating surface;

patterning said semiconductor film into a patterned  
semiconductor film having a peripheral portion;

providing defects and/or stress in [a selected region]  
said peripheral portion of said patterned semiconductor film  
simultaneously with said patterning step;

disposing a crystallization promoting material in  
contact with said semiconductor film, said crystallization

promoting material containing a metal;

crystallizing said patterned semiconductor film  
provided with said crystallization promoting material by heating,  
wherein said metal segregates in said [selected region]  
peripheral portion during the crystallization; and

forming an active region of said semiconductor device  
by etching at least said [selected region] peripheral portion  
after said crystallizing.

21. (Amended) A method for manufacturing a  
semiconductor device comprising the steps of:

forming a non-single crystalline semiconductor film on  
an insulating surface;

directing ions of an element which is inert with  
respect to said semiconductor film into a selected region  
[thereof] of said semiconductor film;

disposing a crystallization promoting material in  
contact with said semiconductor film;

crystallizing said semiconductor film by heating  
wherein said [metal] crystallization promoting material  
segregates in said selected region during the crystallization;  
and

forming an active region of said semiconductor device  
by removing at least said selected region by etching.

Please add the following claims.

-- 22. A method for manufacturing a semiconductor device comprising the steps of:

forming a non-single crystalline semiconductor film on an insulating surface provided over a quartz substrate;

patterning said semiconductor film into a patterned semiconductor film having peripheral portions;

disposing a crystallization promoting material in contact with said semiconductor film either before or after said patterning, said crystallization promoting material containing a metal;

crystallizing said patterned semiconductor film provided with said crystallization promoting material by heating at a temperature of 800 to 1100°C; and

etching the peripheral portions of said patterned semiconductor film after said crystallizing.

23. A method for manufacturing a semiconductor device comprising the steps of:

forming a non-single crystalline semiconductor film on an insulating surface provided over a quartz substrate;

patterning said semiconductor film into a patterned semiconductor film having a peripheral portion;

providing defects and/or stress in said peripheral portion of said patterned semiconductor film simultaneously with said patterning step;

disposing a crystallization promoting material in contact with said semiconductor film, said crystallization promoting material containing a metal;

crystallizing said patterned semiconductor film provided with said crystallization promoting material by heating at a temperature of 800 to 1100°C wherein said metal segregates in said peripheral portion during the crystallizing; and

etching said peripheral portion after said crystallizing.

24. A method for manufacturing a semiconductor device comprising the steps of:

forming a non-single crystalline semiconductor film on an insulating surface provided over a quartz substrate;

patterning said semiconductor film into a patterned semiconductor film having a peripheral portion;

providing defects and/or stress in said peripheral portion of said patterned semiconductor film simultaneously with said patterning step;

disposing a crystallization promoting material in contact with said semiconductor film, said crystallization

promoting material containing a metal;

crystallizing said patterned semiconductor film provided with said crystallization promoting material by heating at a temperature of 800 to 1100°C wherein said metal segregates in said peripheral portion during the crystallizing; and

forming an active region of said semiconductor device by etching at least said peripheral portion after said crystallizing.

25. A method for manufacturing a semiconductor device comprising the steps of:

forming a non-single crystalline semiconductor film on an insulating surface provided over a quartz substrate;

directing ions of an element which is inert with respect to said semiconductor film into a selected region of said semiconductor substrate;

disposing a crystallization promoting material in contact with said semiconductor film;

crystallizing said semiconductor film by heating at a temperature of 800 to 1100°C wherein said crystallization promoting material segregates in said selected region during the crystallizing; and

forming an active region of said semiconductor device by removing at least said selected region by etching.--